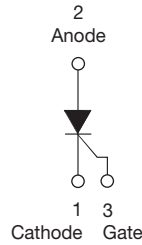


# Thyristor High Voltage, Surface Mount Phase Control SCR, 16 A



### FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according JEDEC-JESD47
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

### DESCRIPTION

The VS-16TTS..SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRODUCT SUMMARY	
Package	TO-263AB (D <sup>2</sup> PAK)
Diode variation	Single SCR
$I_{T(AV)}$	10 A
$V_{DRM}/V_{RRM}$	800 V, 1200 V
$V_{TM}$	1.4 V
$I_{GT}$	60 mA
$T_J$	- 40 °C to 125 °C

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5	A
Aluminum IMS, $R_{thCA} = 15$ °C/W	6.3	9.5	
Aluminum IMS with heatsink, $R_{thCA} = 5$ °C/W	14.0	18.5	

#### Note

- $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	10	A
$I_{RMS}$		16	
$V_{RRM}/V_{DRM}$		800/1200	V
$I_{TSM}$		200	A
$V_T$	10 A, $T_J = 25$ °C	1.4	V
dV/dt		500	V/μs
dI/dt		150	A/μs
$T_J$		- 40 to 125	°C

VOLTAGE RATINGS			
PART NUMBER	$V_{RRM}$ , MAXIMUM PEAK REVERSE VOLTAGE V	$V_{DRM}$ , MAXIMUM PEAK DIRECT VOLTAGE V	$I_{RRM}/I_{DRM}$ AT 125 °C mA
VS-16TTS08SPbF	800	800	10
VS-16TTS12SPbF	1200	1200	



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS	
			TYP.	MAX.		
Maximum average on-state current	$I_{T(AV)}$	$T_C = 98\text{ }^\circ\text{C}$ , 180° conduction, half sine wave	10		A	
Maximum RMS on-state current	$I_{RMS}$		16			
Maximum peak, one-cycle, non-repetitive surge current	$I_{TSM}$	10 ms sine pulse, rated $V_{RRM}$ applied	170			
		10 ms sine pulse, no voltage reapplied	200			
Maximum $I^2t$ for fusing	$I^2t$	10 ms sine pulse, rated $V_{RRM}$ applied	144		$A^2s$	
		10 ms sine pulse, no voltage reapplied	200			
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$ , no voltage reapplied	2000		$A^2\sqrt{s}$	
Maximum on-state voltage drop	$V_{TM}$	10 A, $T_J = 25\text{ }^\circ\text{C}$	1.4		V	
On-state slope resistance	$r_t$	$T_J = 125\text{ }^\circ\text{C}$	24.0		$m\Omega$	
Threshold voltage	$V_{T(TO)}$		1.1		V	
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	$T_J = 25\text{ }^\circ\text{C}$	0.5		mA
			$T_J = 125\text{ }^\circ\text{C}$	10		
Holding current	$I_H$	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$	-	150		
Maximum latching current	$I_L$	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	200			
Maximum rate of rise of off-state voltage	$dV/dt$	$T_J = T_{J\text{ max}}$ . linear to 80 % $V_{DRM} = R_g - k = \text{Open}$	500		$V/\mu s$	
Maximum rate of rise of turned-on current	$dI/dt$		150		$A/\mu s$	

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	+ $I_{GM}$		1.5	A
Maximum peak negative gate voltage	- $V_{GM}$		10	V
Maximum required DC gate current to trigger	$I_{GT}$	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	90	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	60	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	35	
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	3.0	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	2.0	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	1.0	
Maximum DC gate voltage not to trigger	$V_{GD}$	$T_J = 125\text{ }^\circ\text{C}$ , $V_{DRM} = \text{Rated value}$	0.25	
Maximum DC gate current not to trigger	$I_{GD}$		2.0	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	$t_{gt}$	$T_J = 25\text{ }^\circ\text{C}$	0.9	$\mu s$
Typical reverse recovery time	$t_{rr}$	$T_J = 125\text{ }^\circ\text{C}$	4	
Typical turn-off time	$t_q$		110	

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$		- 40 to 125	°C
Soldering temperature	$T_S$	For 10 s (1.6 mm from case)	260	
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation	1.3	°C/W
Typical thermal resistance, junction to ambient	$R_{thJA}$	PCB mount <sup>(1)</sup>	40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D <sup>2</sup> PAK (SMD-220)	16TTS08S	
			16TTS12S	

**Note**

- <sup>(1)</sup> When mounted on 1" square (650 mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994.

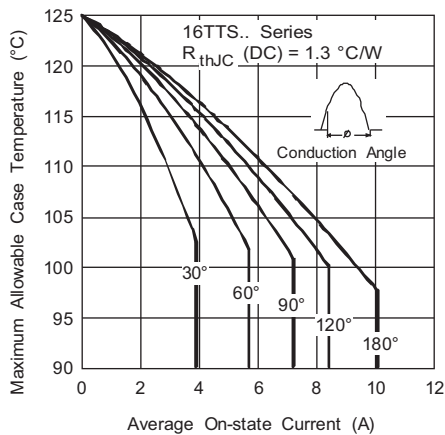


Fig. 1 - Current Rating Characteristics

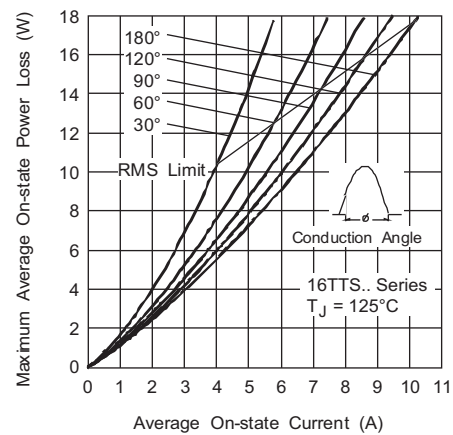


Fig. 3 - On-State Power Loss Characteristics

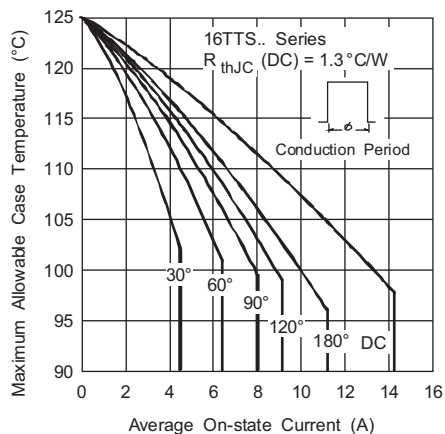


Fig. 2 - Current Rating Characteristics

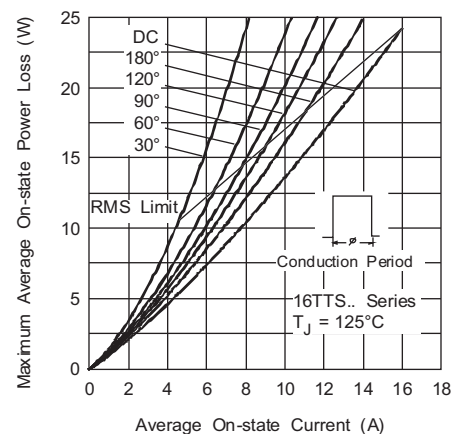


Fig. 4 - On-State Power Loss Characteristics

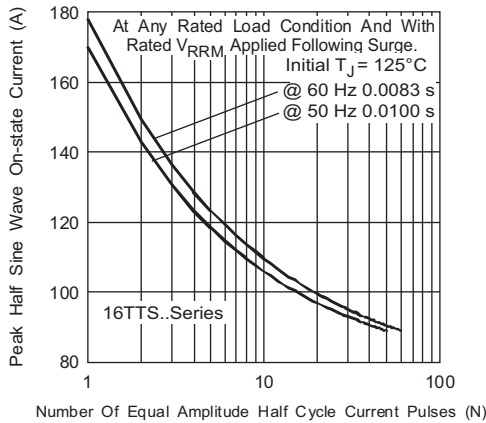


Fig. 5 - Maximum Non-Repetitive Surge Current

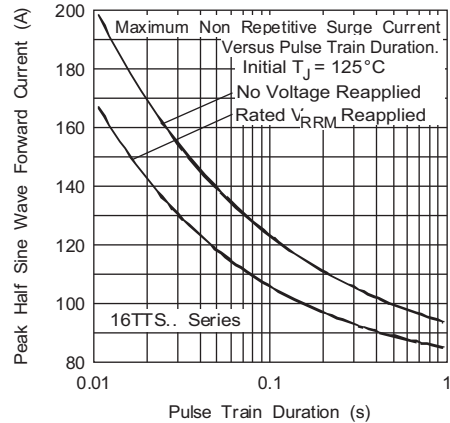


Fig. 6 - Maximum Non-Repetitive Surge Current

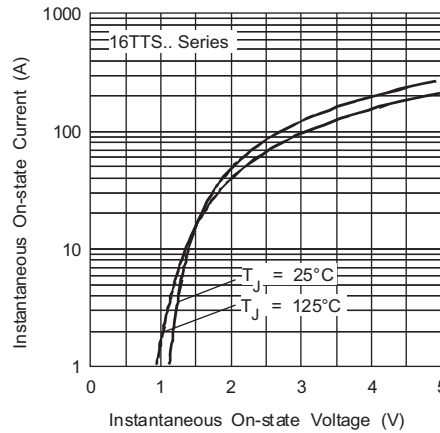


Fig. 7 - On-State Voltage Drop Characteristics

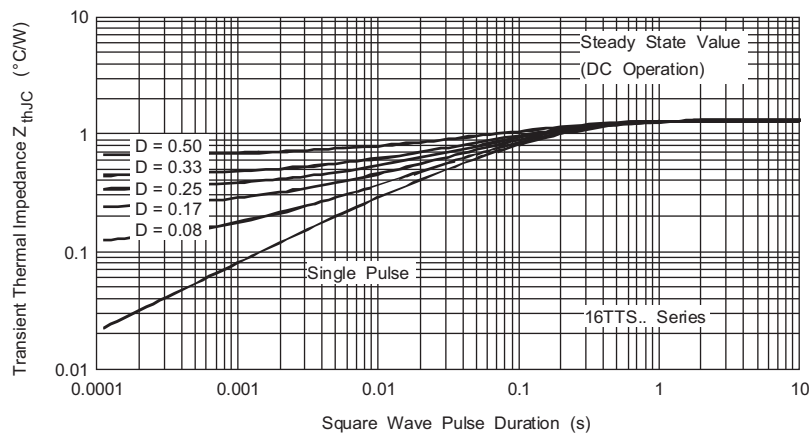


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

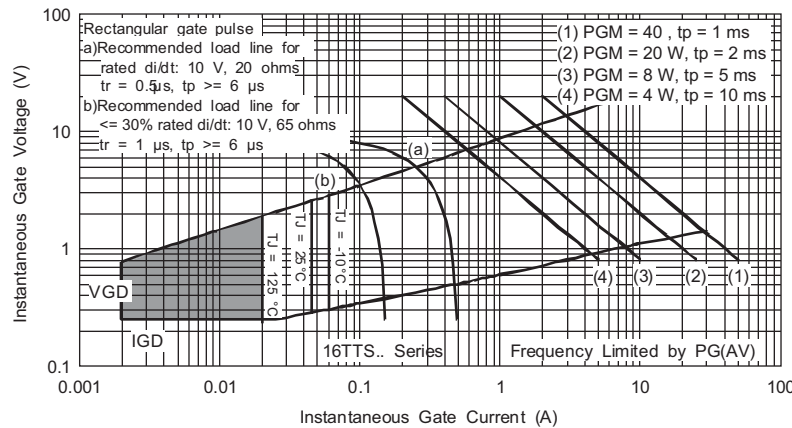


Fig. 9 - Gate Characteristics

### ORDERING INFORMATION TABLE

Device code	<b>VS-</b>	<b>16</b>	<b>T</b>	<b>T</b>	<b>S</b>	<b>12</b>	<b>S</b>	<b>TRL</b>	<b>PbF</b>
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Vishay Semiconductors product
- 2** - Current rating
- 3** - Circuit configuration:  
T = Single thyristor
- 4** - Package:  
T = TO-220AC
- 5** - Type of silicon:  
S = Standard recovery rectifier
- 6** - Voltage rating: Voltage code x 100 =  $V_{RRM}$
- 7** - S = D<sup>2</sup>PAK version
- 8** -
  - None = Tube
  - TRL = Tape and reel (left oriented)
  - TRR = Tape and reel (right oriented)
- 9** - PbF = Lead (Pb)-free and RoHS compliant

08 = 800 V
12 = 1200 V

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-16TTS08SPbF	50	1000	Antistatic plastic tubes
VS-16TTS08STRRPbF	800	800	13" diameter reel
VS-16TTS08STRLPbF	800	800	13" diameter reel
VS-16TTS12SPbF	50	1000	Antistatic plastic tubes
VS-16TTS12STRRPbF	800	800	13" diameter reel
VS-16TTS12STRLPbF	800	800	13" diameter reel

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95046">www.vishay.com/doc?95046</a>
Part marking information	<a href="http://www.vishay.com/doc?95054">www.vishay.com/doc?95054</a>
Packaging information	<a href="http://www.vishay.com/doc?95032">www.vishay.com/doc?95032</a>

## D<sup>2</sup>PAK

### DIMENSIONS in millimeters and inches

Conforms to JEDEC outline D<sup>2</sup>PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

### Notes

- Dimensioning and tolerancing per ASME Y14.5 M-1994
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- Thermal pad contour optional within dimension E, L1, D1 and E1
- Dimension b1 and c1 apply to base metal only
- Datum A and B to be determined at datum plane H
- Controlling dimension: inch
- Outline conforms to JEDEC outline TO-263AB



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